	Hits	Search Text	DBs	
,		(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems	USPAT; US-PGPUB	
¹,		photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2)))		
2	83	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2))) and (((semiconductor silicon adj nitride polycrystaline adj silicon) near2 layer\$1) (layers with symmet\$5) (layers with (odd\$1number (odd near2 number))))	USPAT; US-PGPUB	
3	25	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2))) and (((semiconductor silicon adj nitride polycrystaline adj silicon) near2 layer\$1) (layers with symmet\$5) (layers with (odd\$1number (odd near2 number)))) and actuat\$3	USPAT; US-PGPUB	
4	6	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2))) and (((semiconductor silicon adj nitride polycrystaline adj silicon) near2 layer\$1) (layers with symmet\$5) (layers with (odd\$1number (odd near2 number)))) and (odd\$1number (odd near2 number))	USPAT: US-PGPUB	
5	3	(((deformable flexible freestanding multi\$11ayer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$11ayer\$2))) and (layers with (odd\$1number (odd near2 number)))	USPAT: US-PGPUB	
6	1	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2))) and (((semiconductor dielectric silicon adj nitride polycrystaline adj silicon) near2 layer\$1) same ((layers multi\$1layers) with (odd\$1number (odd near2 number))))	USPAT; US-PGPUB	
7	35	freestanding adj membrane	USPAT; US-PGPUB	
8	50	((semiconductor dielectric silicon adj nitride polycrystaline adj silicon) near2 layer\$1) same ((layers multi\$1layers) with (odd\$1number (odd near2 number)))	USPAT; US-PGPUB	
9	11	((semiconductor dielectric silicon adj nitride polycrystaline adj silicon) near2 layer\$1) same ((layers multi\$1layers) with (odd\$1number (odd near2 number))) and ((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film))	USPAT; US-PGPUB	
10	14	((deformable flexible freestanding) near2 (film membrane pellicle (thin adj film) thin\$1film)) and (layers with (odd\$1number (odd near2 number)))	USPAT; US-PGPUB	
11	75	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2)))	EPO; JPO; DERWENT	
12	2	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2))) and (((semiconductor silicon adj nitride polycrystaline adj silicon) near2 layer\$1) (layers with symmet\$5) (layers with (odd\$1number (odd near2 number))))	EPO; JPO; DERWENT	
13	2	freestanding adj membrane	EPO; JPO; DERWENT	
14	18	((semiconductor dielectric silicon adj nitride polycrystaline adj silicon) near2 layer\$1) same ((layers multi\$1layers) with (odd\$1number (odd near2 number)))	EPO; JPO; DERWENT	
15	4	((semiconductor dielectric silicon adj nitride polycrystaline adj silicon) near2 layer\$1) same ((layers multi\$1layers) with (odd\$1number (odd near2 number))) and ((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film))	EPO; JPO; DERWENT	
16	1	("20030045036").PN.	USPAT; US-PGPUB	
17	13	((semiconductor dielectric silicon adj nitride polycrystaline adj silicon) near2 layer\$1) same ((layers multi\$1layers) with (odd\$1number (odd near2 number)) same (mirror\$ micro\$1mirror\$1))	USPAT; US-PGPUB	
18	15	(((semiconductor dielectric silicon adj nitride polycrystaline adj silicon) near2 layer\$1) with (odd\$1number (odd near2 number))) and 359/(290-298).ccls.	USPAT; US-PGPUB	
19	153	((semiconductor dielectric silicon adj nitride polycrystaline adj silicon) with mirror) and ((359/290).ccls.(359/291).ccls. (359/292).ccls. (359/293).ccls. (359/294).ccls. (359/295).ccls. (359/298).ccls.)	USPAT; US-PGPUB	
20	77	((semiconductor dielectric silicon adj nitride polycrystaline adj silicon) with mirror with layer\$1) and ((359/290).ccls.(359/291).ccls. (359/292).ccls. (359/293).ccls. (359/294).ccls. (359/295).ccls. (359/298).ccls.)	USPAT; US-PGPUB	
21	7	intpax.as.	USPAT; US-PGPUB	
22	26	(elm adj technology).as.	USPAT; US-PGPUB	
23	5	("4756602"   "5023944"   "5144498"   "5583683"   "5719989").PN.	USPAT	
24	5	("4756602"   "5023944"   "5144498"   "5583683"   "5719989").PN.	USPAT	

	Hits	Search Text	DBs
25	5	("4756602"   "5023944"   "5144498"   "5583683"   "5719989").PN.	USPAT
26	4	("5144498"   "5212584"   "5410431"   "5583683").PN.	USPAT
27	6	5999322.URPN.	USPAT
28	591	(359/291).CCLS.	USPAT; US-PGPUB
29	199	(359/321).CCLS.	USPAT; US-PGPUB
30	454	(359/580).CCLS.	USPAT; US-PGPUB
31	372	(359/586).CCLS.	USPAT; US-PGPUB
32	241	(359/588).CCLS.	USPAT; US-PGPUB
33	714	(216/13).CCLS.	USPAT; US-PGPUB
34	560	(216/24).CCLS.	USPAT; US-PGPUB
35	402	(438/29),CCLS.	USPAT; US-PGPUB

	1 2 C 3 Document	Title	Current OR
1		Optical thin-film cavities for transducing visible radiation to infrared radiation	385/119
2	US 6558868 B2	Method of fabricating a high aspect ratio microstructure	430/259
3	<b>XIII</b> US 6556338 B2	MEMS based variable optical attenuator (MBVOA)	359/298
4	<b>⊠</b> US 6509998 B2	Tunable multi-channel optical attenuator (TMCOA) .	359/245
5	US 6373632 B1	Tunable Fabry-Perot filter	359/578
6	II	Fabrication of broadband surface-micromachined micro-electro-mechanical switches for microwave and millimeter-wave applications	216/13
7	US 6046659 A	Design and fabrication of broadband surface-micromachined micro-electro-mechanical switches for microwave and millimeter-wave applications	333/262
8	US 5999322 A	Multilayer thin film bandpass filter	359/589
9		Robust multi-layered thin-film membrane for micro-electromechanical systems (MEMS) photonic devices	438/149
10		Fabry-Perot cavity manufactured with bulk micro-machining process applied on supporting substrate	359/321
11		Microelectromechanically tunable, confocal, vertical cavity surface emitting laser and fabry-perot filter	372/20
12	US 20020191929 A1	Omnidirectional multilayer device for enhanced optical waveguiding	385/127
13		Method for attenuation of optical signals using reflective membrane device	385/140
14	XI I US 20020122252 A1	Optical bodies made with a birefringent polymer	359/498
15		Defined sacrifical region via ion implantation for micro-opto-electro-mech- anical system (MOEMS) applications	438/57
16	US 20020080504 A1	Triple electrode MOEMS tunable filter and fabrication process therefor	359/872
17	US 20020080465 A1	MEMS based variable optical attenuator (MBVOA)	359/291
18	U5 20020071463 A1	Surface-emitting semiconductor laser	372/45
19	<b>⊠</b> US 20020054416 A1	Tunable multi-channel optical attenuator (TMCOA)	359/245
I	JP 2000232236 A	NITRIDE SEMICONDUCTOR ELEMENT	